

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Amendments to the Claims.

Sub D1
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1. (Currently Amended): A method, comprising:

cleaning a plasma reactor chamber part of a material redistributed thereon by a reactive plasma process, by placing the chamber part in a redistributed material solvent for at least 6 hours.

2. The method of claim 1, wherein:

the material includes photoresist polymers and the solvent includes acetone.

3. The method of claim 1, wherein:

the chamber part comprises quartz.

4. (Cancelled): The method of claim 1, wherein:

the chamber part is placed in the solvent for at least 6 hours.

5. The method of claim 1, further including:

cleaning the chamber part with a plasma that includes oxygen as a source gas.

6. The method of claim 5, wherein:

the plasma is formed with a radio frequency (RF) power in the general range of 500 to 1000 W.

7. The method of claim 5, further including:

rinsing the chamber part after cleaning with the solvent but before the plasma cleaning.

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- Sub D1
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8. The method of claim 1, further including:
ultrasonically cleaning the chamber part.
9. The method of claim 1, further including:
baking the chamber part at a temperature in the general range of 75-150
°C.

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10. (Currently Amended): A method of cleaning a plasma reactor chamber part, comprising:
plasma cleaning a chamber part of a material redistributed on the
chamber part by a reactive plasma process, with a plasma having an etch
selectivity between the chamber part and the redistributed material that is
greater than 1:100; and
cleaning the chamber part with a solvent of the redistributed
material by placing the chamber part in the solvent of the redistributed
material.
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11. The method of claim 10, wherein:
the chamber part comprises quartz and the plasma includes oxygen as
a source gas.

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12. The method of claim 10, wherein:
the plasma is formed with a radio frequency (RF) power in the general
range of 500 to 1000 W.

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13. The method of claim 10, wherein:
the redistributed material includes photoresist polymers.

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14. (Cancelled) The method of claim 10, further including:
cleaning the chamber part with a solvent of the redistributed material.

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15. (Currently Amended) A method of cleaning reactive plasma chamber parts, comprising the steps of:

applying an organic solvent to a surface of a chamber part; and
oxygen plasma cleaning the chamber part; and
ultrasonically cleaning the chamber part after the oxygen plasma
cleaning.

5 16. The method of claim 15, wherein:
the organic solvent includes acetone.

17. (Cancelled) The method of claim 15, further including:
rinsing the chamber part with de-ionized water after applying the
10 organic solvent.

18. The method of claim 15, further including:
ultrasonically cleaning the chamber part after the oxygen plasma cleaning.

15 19. The method of claim 18, further including:
rinsing the chamber part with a liquid that evaporates at a lower
temperature than water after the ultrasonic cleaning.

20. The method of claim 15, further including:
20 baking the chamber part at a temperature greater than 80 °C for at least
15 minutes.

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